

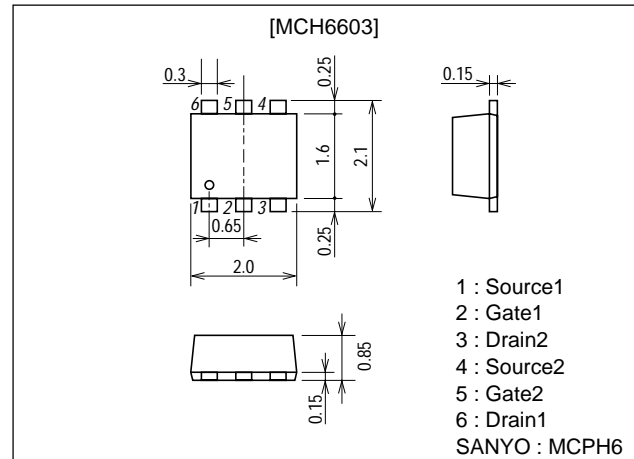
**MCH6603****Ultrahigh-Speed Switching Applications****Features**

- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.
- Composite type with 2 MOSFETs contained in one package, facilitating high-density mounting.

Package Dimensions

unit:mm

2173

**Specifications****Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-50	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		-0.14	A
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	-0.56	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm) 1unit	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0$	-50			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-50V, V_{GS}=0$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-100\mu A$	-0.4		-1.4	V
Forward Transfer Admittance	yfs	$V_{DS}=-10V, I_D=-40mA$	70	110		mS
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-40mA, V_{GS}=-4V$		18	23	Ω
	$R_{DS(on)2}$	$I_D=-20mA, V_{GS}=-2.5V$		20	28	Ω
	$R_{DS(on)3}$	$I_D=-5mA, V_{GS}=-1.5V$		30	60	Ω

Marking : FC

Continued on next page.

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SANYO Electric Co.,Ltd. Semiconductor Company

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

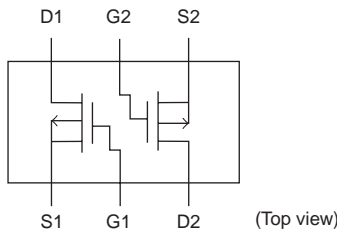
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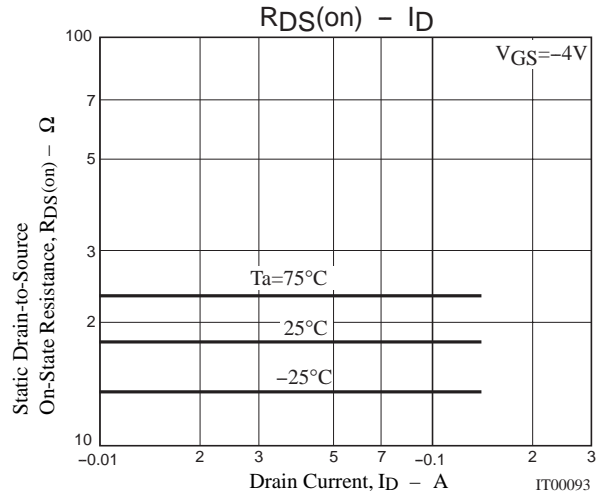
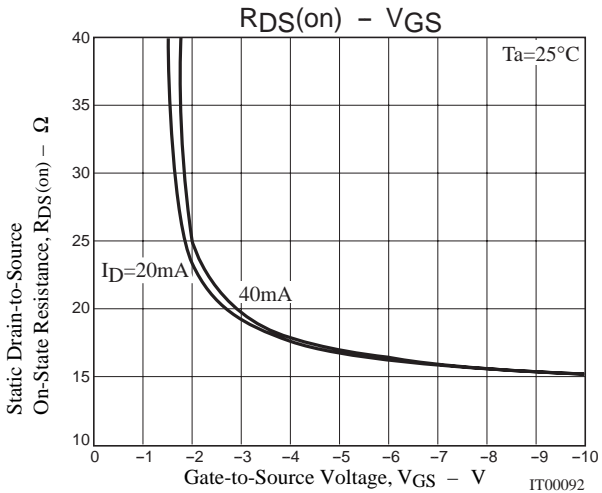
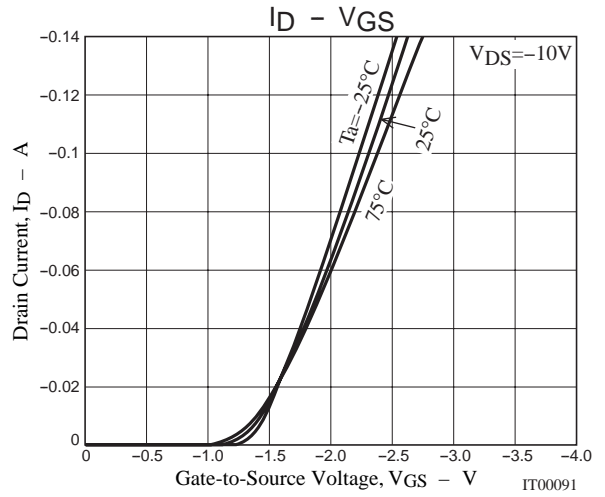
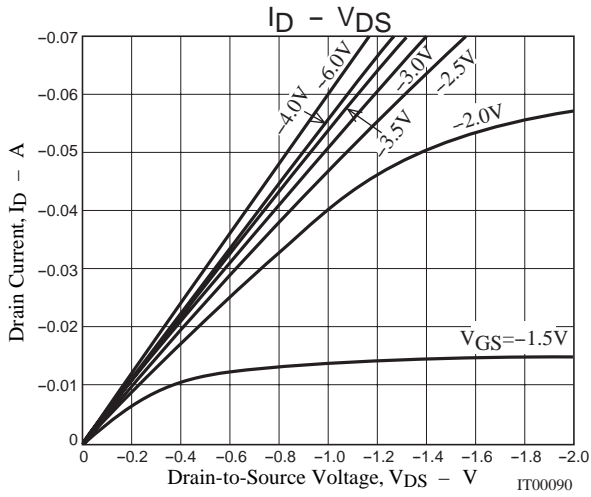
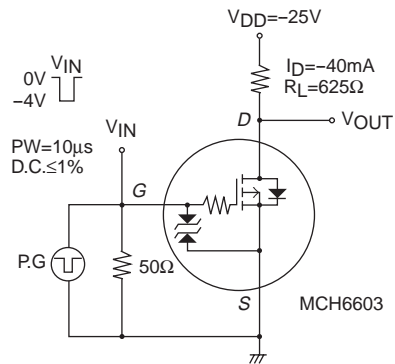
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=-10V, f=1MHz$		7.4		pF
Output Capacitance	Coss	$V_{DS}=-10V, f=1MHz$		4.2		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=-10V, f=1MHz$		1.3		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		20		ns
Rise Time	t_r	See specified Test Circuit		35		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		160		ns
Fall Time	t_f	See specified Test Circuit		150		ns
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		1.40		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		0.16		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		0.23		nC
Diode Forward Voltage	V_{SD}	$I_S=-70mA, V_{GS}=0$		0.85	1.2	V

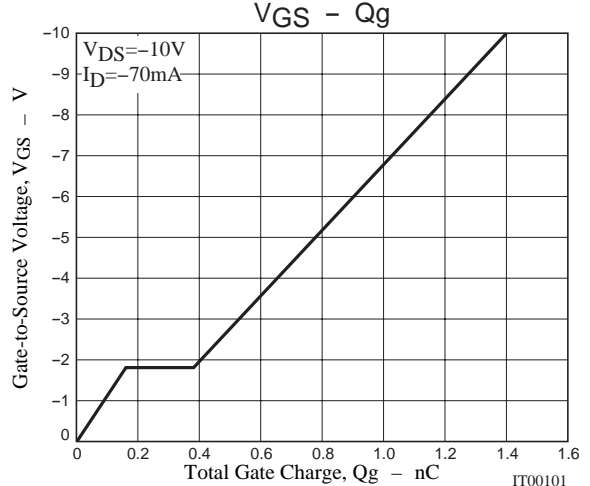
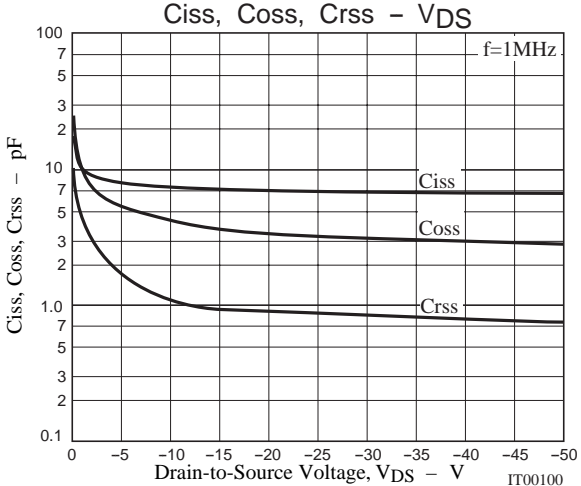
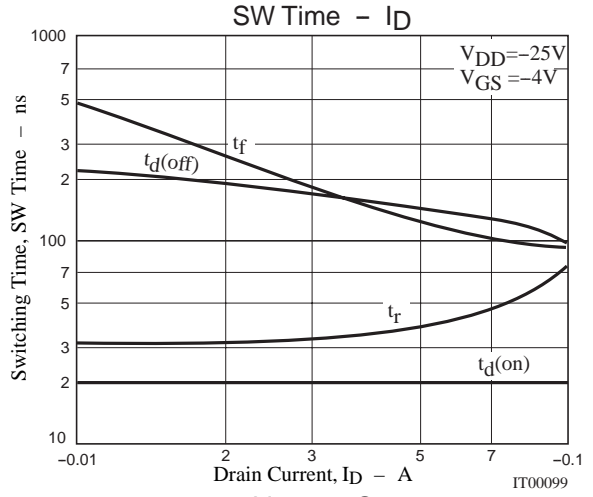
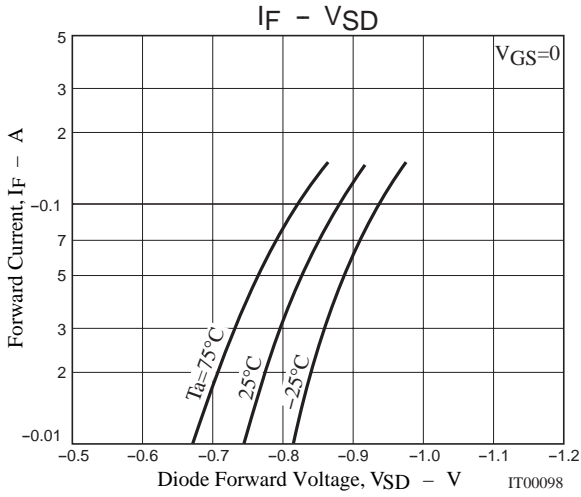
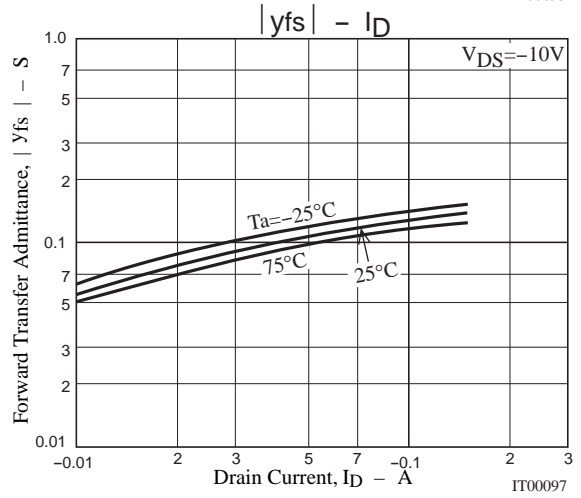
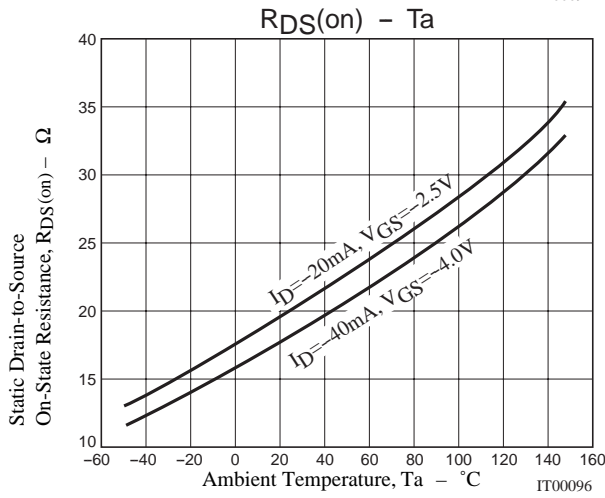
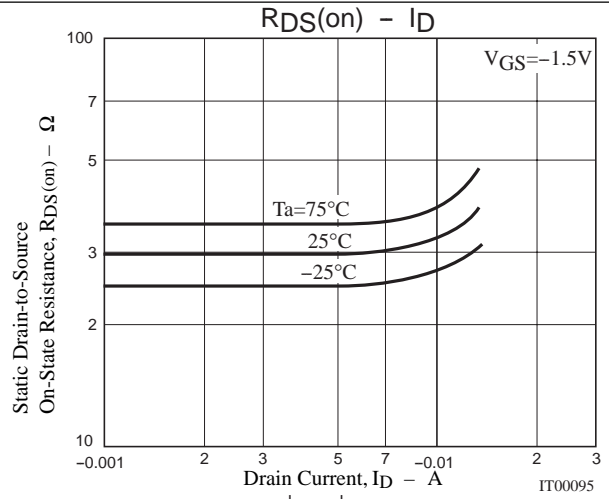
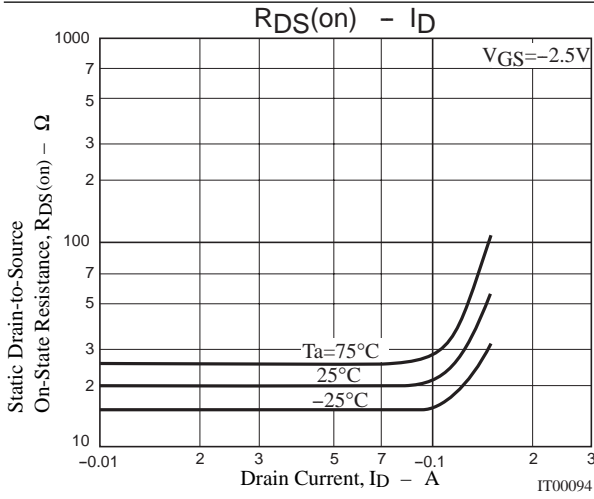
Electrical Connection



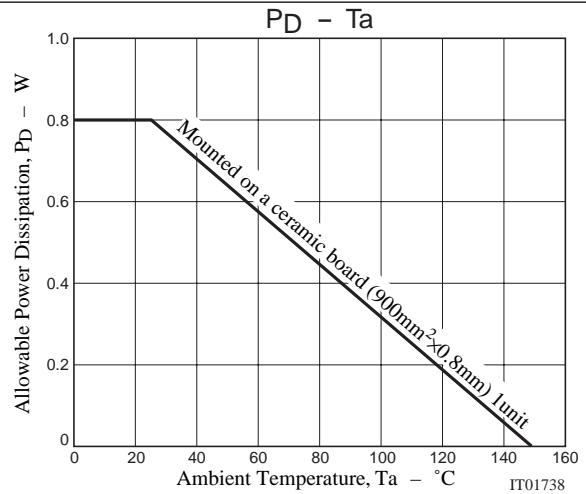
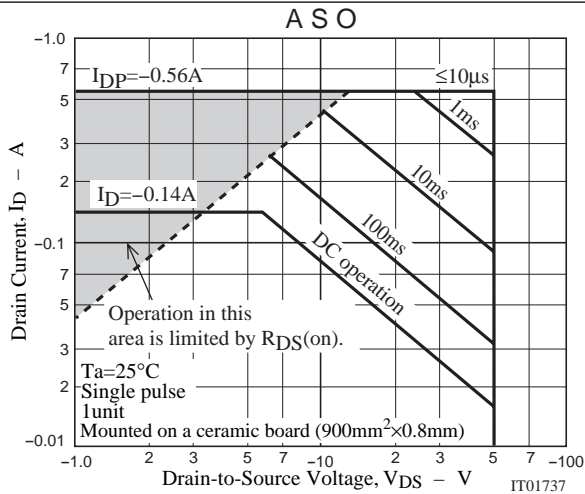
Switching Time Test Circuit



MCH6603



MCH6603



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